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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	51
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TFBGA
Supplier Device Package	64-TFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l072rbh6tr

3.3 ARM® Cortex®-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit ARM Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded ARM core, the STM32L072xx are compatible with all ARM tools and software.

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L072xx embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

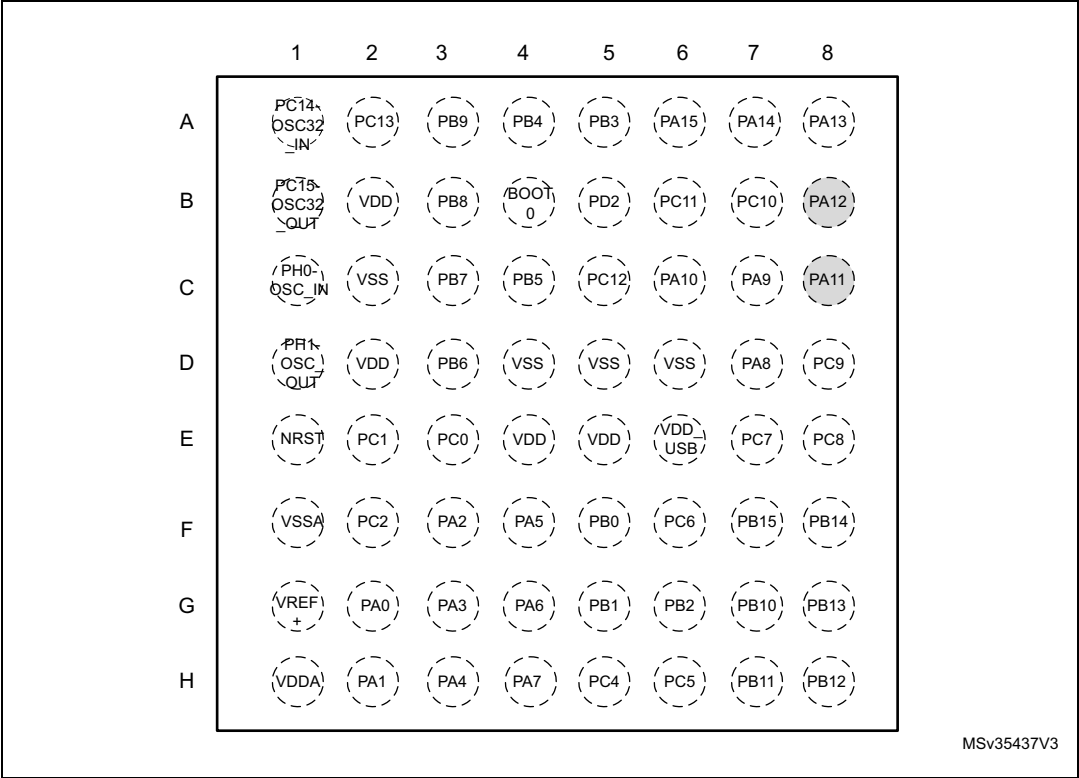
- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

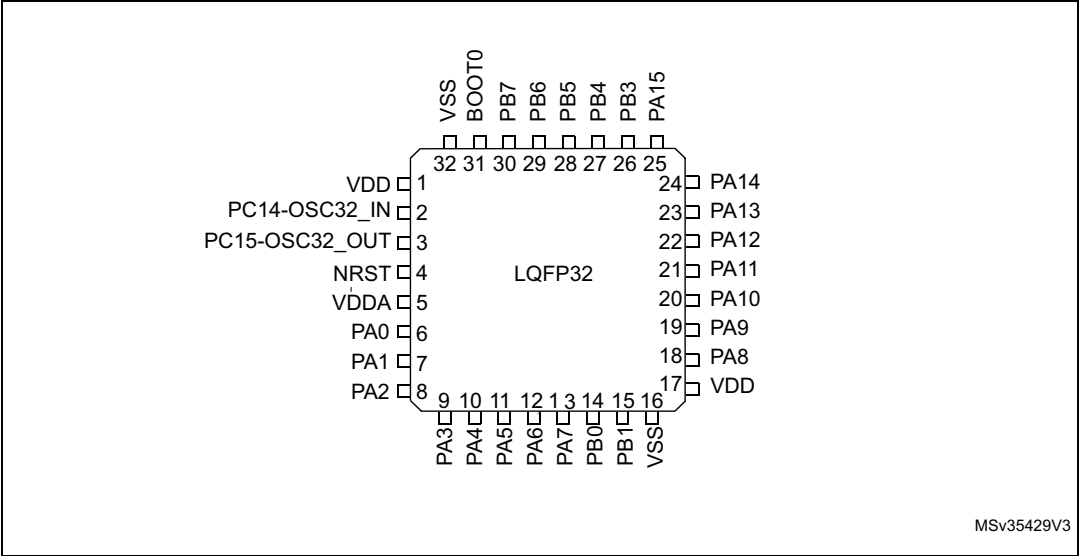
This hardware block provides flexible interrupt management features with minimal interrupt latency.

Figure 6. STM32L072xx UFBGA64/TFBGA64 ballout - 5x 5 mm



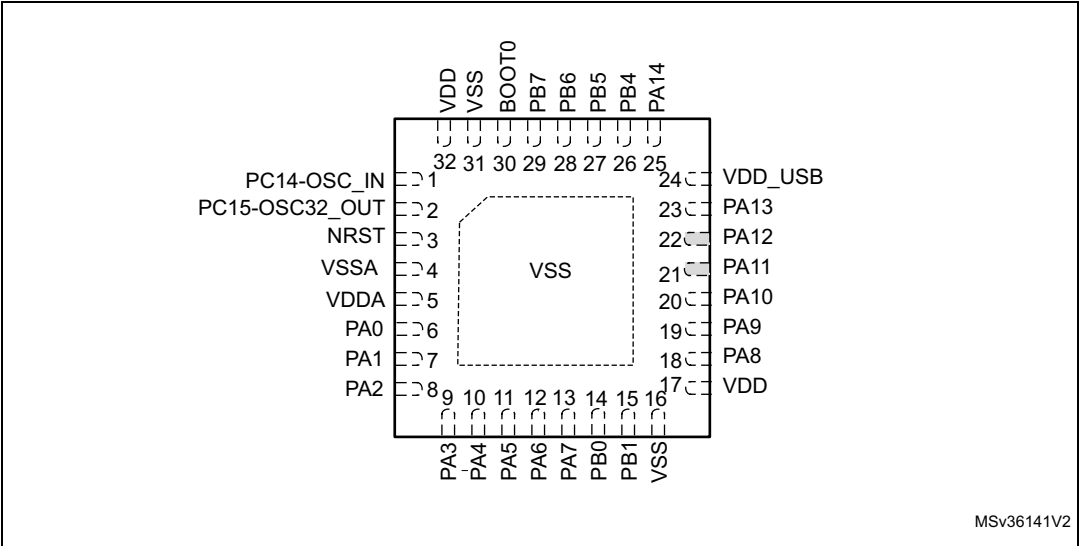
1. The above figure shows the package top view.
2. I/O pin supplied by VDD_USB.

Figure 9. STM32L072xx LQFP32 pinout



1. The above figure shows the package top view.

Figure 10. STM32L072xx UFQFPN32 pinout



1. The above figure shows the package top view.
2. I/O pin supplied by VDD_USB.

Table 15. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		FTf	5 V tolerant I/O, FM+ capable
		TC	Standard 3.3V I/O
		B	Dedicated BOOT0 pin
		RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes		Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 16. STM32L072xxx pin definition

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	LQFP64	UFBGA64/TFBGA64	WLCSP49	LQFP100	UFBG100						
-	-	-	-	-	-	1	B2	PE2	I/O	FT	-	TIM3_ETR	-
-	-	-	-	-	-	2	A1	PE3	I/O	FT	-	TIM22_CH1, TIM3_CH1	-
-	-	-	-	-	-	3	B1	PE4	I/O	FT	-	TIM22_CH2, TIM3_CH2	-
-	-	-	-	-	-	4	C2	PE5	I/O	FT	-	TIM21_CH1, TIM3_CH3	-
-	-	-	-	-	-	5	D2	PE6	I/O	FT	-	TIM21_CH2, TIM3_CH4	RTC_TAMP3/WKUP3
1	-	1	1	B2	B6	6	E2	VDD	S		-	-	-

Table 16. STM32L072xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	LQFP64	UFBGA64/TFBGA64	WLCSP49	LQFP100	UFBG100						
-	-	-	-	-	-	60	H12	PD13	I/O	FT	-	-	-
-	-	-	-	-	-	61	H11	PD14	I/O	FT	-	-	-
-	-	-	-	-	-	62	H10	PD15	I/O	FT	-	USB_CRD_SYNC	-
-	-	-	37	F6	-	63	E12	PC6	I/O	FT	-	TIM22_CH1, TIM3_CH1, TSC_G8_IO1	-
-	-	-	38	E7	-	64	E11	PC7	I/O	FT	-	TIM22_CH2, TIM3_CH2, TSC_G8_IO2	-
-	-	-	39	E8	-	65	E10	PC8	I/O	FT	-	TIM22_ETR, TIM3_CH3, TSC_G8_IO3	-
-	-	-	40	D8	-	66	D12	PC9	I/O	FTf	-	TIM21_ETR, USB_OE/TIM3_CH4, TSC_G8_IO4, I2C3_SDA	-
18	18	29	41	D7	D1	67	D11	PA8	I/O	FTf	-	MCO, USB_CRD_SYNC, EVENTOUT, USART1_CK, I2C3_SCL	-
19	19	30	42	C7	E2	68	D10	PA9	I/O	FTf	-	MCO, TSC_G4_IO1, USART1_TX, I2C1_SCL, I2C3_SMBA	-
20	20	31	43	C6	C1	69	C12	PA10	I/O	FTf	-	TSC_G4_IO2, USART1_RX, I2C1_SDA	-
21	21	32	44	C8	D2	70	B12	PA11	I/O	FT	⁽³⁾	SPI1_MISO, EVENTOUT, TSC_G4_IO3, USART1_CTS, COMP1_OUT	USB_DM
22	22	33	45	B8	B1	71	A12	PA12	I/O	FT	⁽³⁾	SPI1_MOSI, EVENTOUT, TSC_G4_IO4, USART1_RTS_DE, COMP2_OUT	USB_DP
23	23	34	46	A8	C2	72	A11	PA13	I/O	FT	-	SWDIO, USB_OE, LPUART1_RX	-
-	-	-	-	-	-	73	C11	VDD	S		-	-	-
-	-	35	47	D5	-	74	F11	VSS	S		-	-	-

Table 16. STM32L072xxx pin definition (continued)

Pin number								Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32 ⁽¹⁾	LQFP48	LQFP64	UFBGA64/TFBGA64	WLCSP49	LQFP100	UFBG100						
27	26	40	56	A4	B3	90	A7	PB4	I/O	FTf	-	SPI1_MISO, TIM3_CH1, TSC_G5_IO2, TIM22_CH1, USART1_CTS, USART5_RX, I2C3_SDA	COMP2_INP
28	27	41	57	C4	A4	91	C5	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM3_CH2/TIM22_CH2, USART1_CK, USART5_CK/USART5_R TS_DE	COMP2_INP
29	28	42	58	D3	B4	92	B5	PB6	I/O	FTf	-	USART1_TX, I2C1_SCL, LPTIM1_ETR, TSC_G5_IO3	COMP2_INP
30	29	43	59	C3	C3	93	B4	PB7	I/O	FTf	-	USART1_RX, I2C1_SDA, LPTIM1_IN2, TSC_G5_IO4, USART4_CTS	COMP2_INP, VREF_PVD_IN
31	30	44	60	B4	A5	94	A4	BOOT0	I		-	-	-
-	-	45	61	B3	B5	95	A3	PB8	I/O	FTf	-	TSC_SYNC, I2C1_SCL	-
-	-	46	62	A3	A6	96	B3	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-
-	-	-	-	-	-	97	C3	PE0	I/O	FT	-	EVENTOUT	-
-	-	-	-	-	-	98	A2	PE1	I/O	FT	-	EVENTOUT	-
32	31	47	63	D4	-	99	D3	VSS	S	-	-	-	-
-	32	48	64	E4	A7	100	C4	VDD	S	-	-	-	-

1. UFQFPN32 pinout differs from other STM32 devices except STM32L07xxx and STM32L8xxx.

2. PA4 offers a reduced touch sensing sensitivity. It is thus recommended to use it as sampling capacitor I/O.

3. These pins are powered by VDD_USB. For all characteristics that refer to V_{DD}, V_{DD_USB} must be used instead.

Table 26. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
P _D	Power dissipation at T _A = 85 °C (range 6) or T _A = 105 °C (range 7) ⁽⁴⁾	UFBGA100 package	-	351	mW
		LQFP100 package	-	488	
		UFBG64 package	-	308	
		TFBGA64 package	-	313	
		LQFP64 package	-	435	
		WLCSP49 package	-	417	
		LQFP48 package	-	370	
		UFQFPN32 package	-	556	
		LQFP32 package	-	333	
	Power dissipation at T _A = 125 °C (range 3) ⁽⁴⁾	UFBGA100 package	-	88	
		LQFP100 package	-	122	
		UFBG64 package	-	77	
		TFBGA64 package	-	78	
		LQFP64 package	-	109	
		WLCSP49 package	-	104	
		LQFP48 package	-	93	
		UFQFPN32 package	-	139	
		LQFP32 package	-	83	
T _A	Temperature range	Maximum power dissipation (range 6)	-40	85	°C
		Maximum power dissipation (range 7)	-40	105	
		Maximum power dissipation (range 3)	-40	125	
T _J	Junction temperature range (range 6)	-40 °C ≤ T _A ≤ 85 °	-40	105	
	Junction temperature range (range 7)	-40 °C ≤ T _A ≤ 105 °C	-40	125	
	Junction temperature range (range 3)	-40 °C ≤ T _A ≤ 125 °C	-40	130	

1. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.
2. V_{DD_USB} must respect the following conditions:
 - When V_{DD} is powered on (V_{DD} < V_{DD_min}), V_{DD_USB} should be always lower than V_{DD}.
 - When V_{DD} is powered down (V_{DD} < V_{DD_min}), V_{DD_USB} should be always lower than V_{DD}.
 - In operating mode, V_{DD_USB} could be lower or higher V_{DD}.
 - If the USB is not used, V_{DD_USB} must range from V_{DD_min} to V_{DD_max} to be able to use PA11 and PA12 as standard I/Os.
3. To sustain a voltage higher than V_{DD}+0.3V, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see [Table 25: Thermal characteristics on page 61](#)).

Table 34. Current consumption in Sleep mode

Symbol	Parameter	Condition		f _{HCLK} (MHz)	Typ	Max ⁽¹⁾	Unit
I _{DD} (Sleep)	Supply current in Sleep mode, Flash memory switched OFF	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range3, Vcore=1.2 V VOS[1:0]=11	1	43,5	110	μA
				2	72	140	
				4	130	200	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	160	220	
				8	305	380	
				16	590	690	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	370	460	
				16	715	840	
				32	1650	2000	
		MSI clock	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	18	93	
				0,524	31,5	110	
				4,2	140	230	
		HSI clock source (16 MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	665	850	
			Range1, Vcore=1.8 V VOS[1:0]=01	32	1750	2100	
	Supply current in Sleep mode, Flash memory switched ON	f _{HSE} = f _{HCLK} up to 16MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range3, Vcore=1.2 V VOS[1:0]=11	1	57,5	130	
				2	84	160	
				4	150	220	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	170	240	
				8	315	400	
				16	605	710	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	380	470	
				16	730	860	
				32	1650	2000	
		MSI clock	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	29,5	110	
				0,524	44,5	120	
				4,2	150	240	
		HSI clock source (16MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	680	930	
			Range1, Vcore=1.8 V VOS[1:0]=01	32	1750	2200	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Figure 18. I_{DD} vs V_{DD} , at $T_A = 25^\circ\text{C}$, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

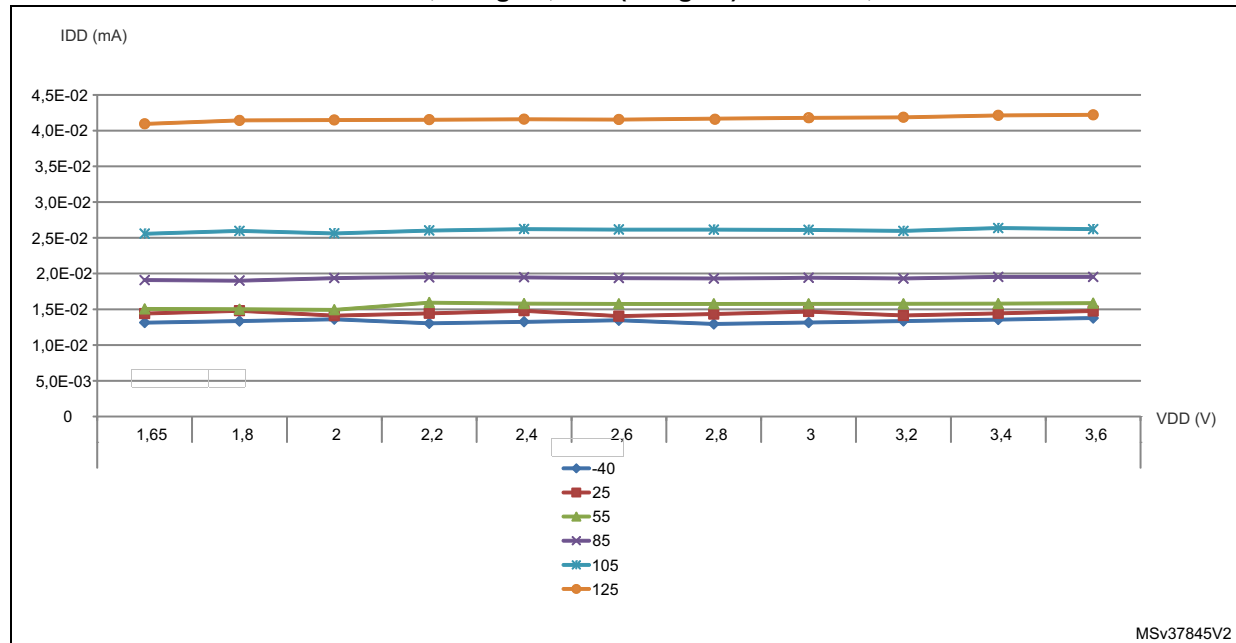


Table 36. Current consumption in Low-power sleep mode

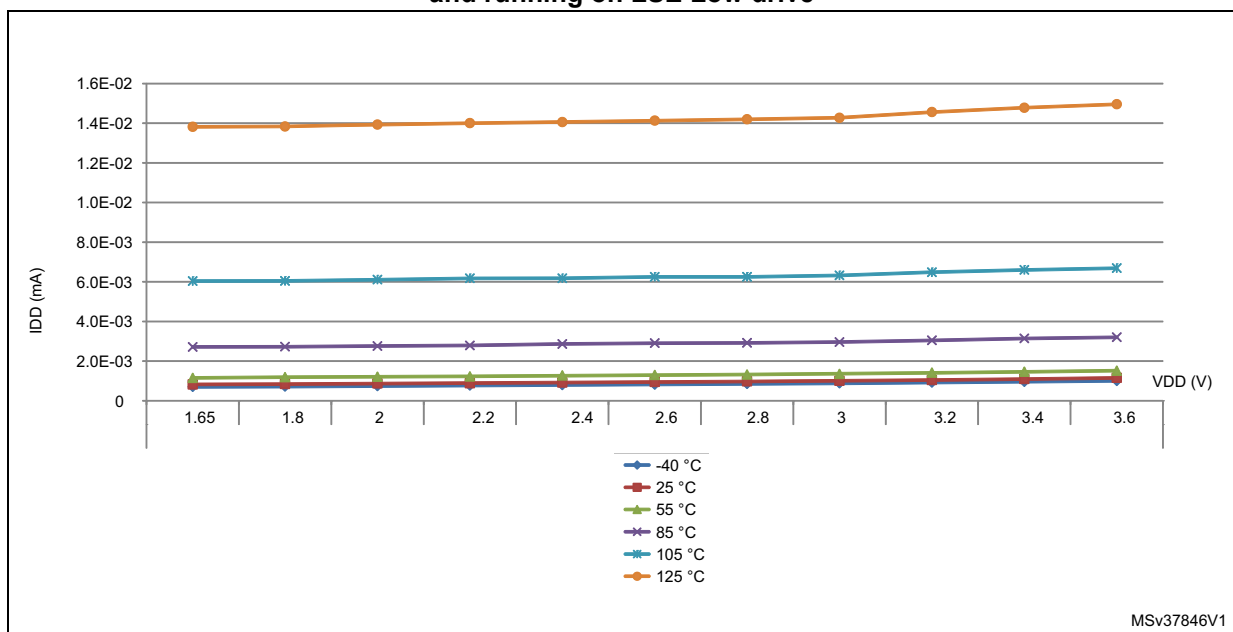
Symbol	Parameter	Condition			Typ	Max (1)	Unit
I_{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, code executed from Flash memory, V_{DD} from 1.65 to 3.6 V	MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz, Flash memory OFF	$T_A = -40$ to 25°C	4,7	-	μA
			MSI clock = 65 kHz, $f_{HCLK} = 32$ kHz	$T_A = -40$ to 25°C	17	24	
				$T_A = 85^\circ\text{C}$	19,5	30	
				$T_A = 105^\circ\text{C}$	23	47	
				$T_A = 125^\circ\text{C}$	32,5	70	
			MSI clock = 65 kHz, $f_{HCLK} = 65$ kHz	$T_A = -40$ to 25°C	17	24	
				$T_A = 85^\circ\text{C}$	20	31	
				$T_A = 105^\circ\text{C}$	23,5	47	
				$T_A = 125^\circ\text{C}$	32,5	70	
			MSI clock = 131kHz, $f_{HCLK} = 131$ kHz	$T_A = -40$ to 25°C	19,5	27	
				$T_A = 55^\circ\text{C}$	20,5	28	
				$T_A = 85^\circ\text{C}$	22,5	33	
				$T_A = 105^\circ\text{C}$	26	50	
				$T_A = 125^\circ\text{C}$	35	73	

1. Guaranteed by characterization results at 125°C , unless otherwise specified.

Table 37. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max ⁽¹⁾	Unit
I_{DD} (Stop)	Supply current in Stop mode	$T_A = -40$ to 25°C	0,43	1,00	μA
		$T_A = 55^\circ\text{C}$	0,735	2,50	
		$T_A = 85^\circ\text{C}$	2,25	4,90	
		$T_A = 105^\circ\text{C}$	5,3	13,00	
		$T_A = 125^\circ\text{C}$	12,5	28,00	

1. Guaranteed by characterization results at 125°C , unless otherwise specified.

Figure 19. I_{DD} vs V_{DD} , at $T_A = 25/55/ 85/105/125^\circ\text{C}$, Stop mode with RTC enabled and running on LSE Low drive

Low-speed external user clock generated from an external source

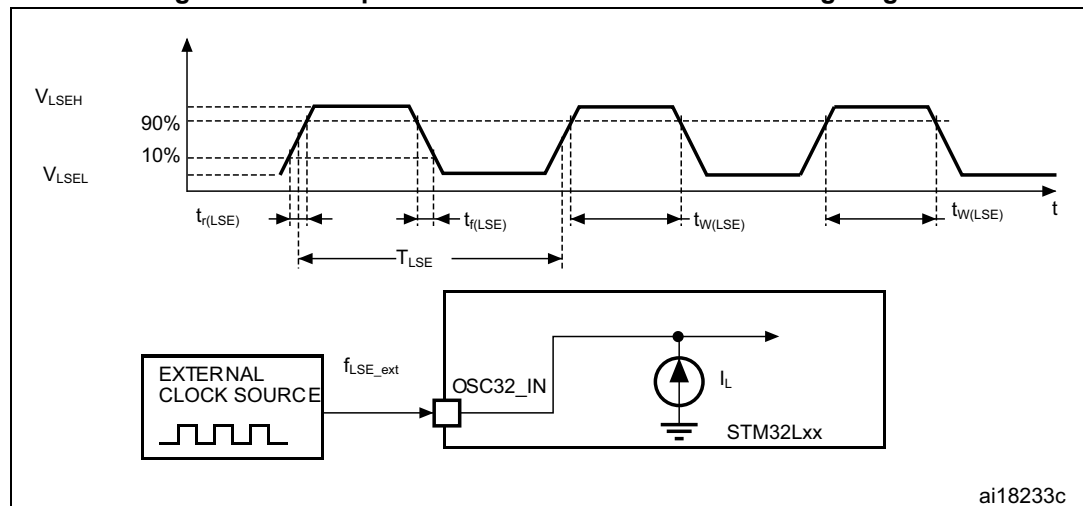
The characteristics given in the following table result from tests performed using a low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 26](#).

Table 44. Low-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{w(LSE)}$	OSC32_IN high or low time		465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time		-	-	10	
$C_{IN(LSE)}$	OSC32_IN input capacitance	-	-	0.6	-	pF
$DuCy_{(LSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design, not tested in production

Figure 22. Low-speed external clock source AC timing diagram



6.3.7 Internal clock source characteristics

The parameters given in [Table 47](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 26](#).

High-speed internal 16 MHz (HSI16) RC oscillator

Table 47. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	Frequency	$V_{DD} = 3.0\text{ V}$	-	16	-	MHz
$TRIM^{(1)(2)}$	HSI16 user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
$ACC_{HSI16}^{(2)}$	Accuracy of the factory-calibrated HSI16 oscillator	$V_{DDA} = 3.0\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$	-1 ⁽³⁾	-	1 ⁽³⁾	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = 0\text{ to }55\text{ }^{\circ}\text{C}$	-1.5	-	1.5	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = -10\text{ to }70\text{ }^{\circ}\text{C}$	-2	-	2	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = -10\text{ to }85\text{ }^{\circ}\text{C}$	-2.5	-	2	%
		$V_{DDA} = 3.0\text{ V}$, $T_A = -10\text{ to }105\text{ }^{\circ}\text{C}$	-4	-	2	%
		$V_{DDA} = 1.65\text{ V to }3.6\text{ V}$ $T_A = -40\text{ to }125\text{ }^{\circ}\text{C}$	-5.45	-	3.25	%
$t_{SU(HSI16)}^{(2)}$	HSI16 oscillator startup time	-	-	3.7	6	μs
$I_{DD(HSI16)}^{(2)}$	HSI16 oscillator power consumption	-	-	100	140	μA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Figure 25. HSI16 minimum and maximum value versus temperature

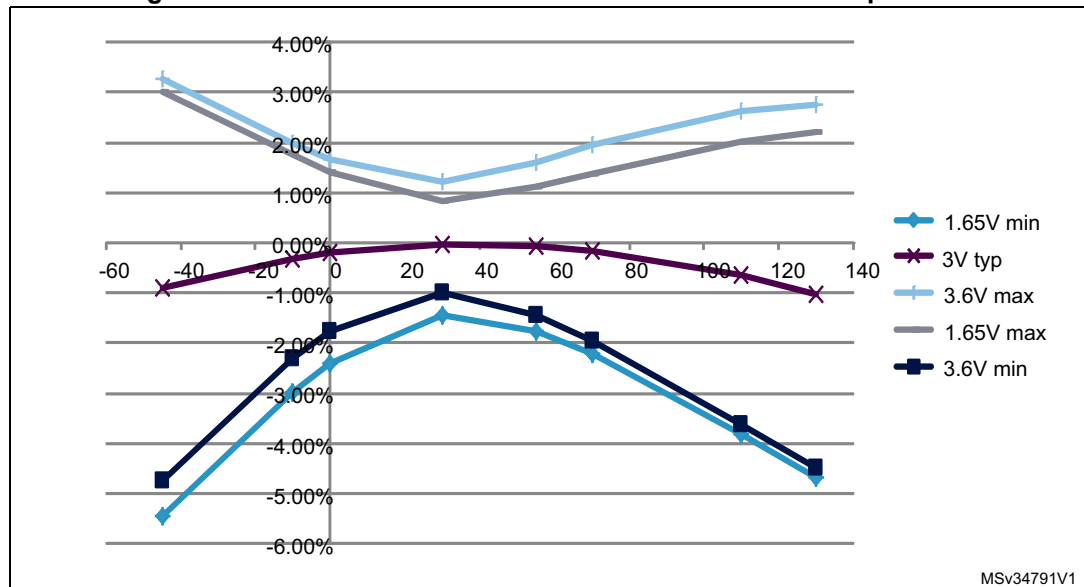


Table 50. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{\text{STAB(MSI)}}^{(2)}$	MSI oscillator stabilization time	MSI range 0	-	40	μs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{\text{OVER(MSI)}}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Guaranteed by characterization results.

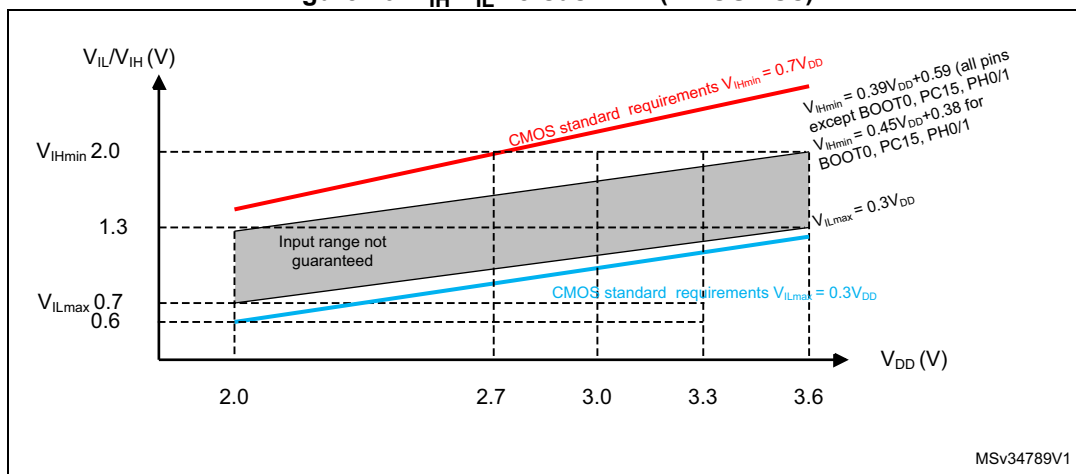
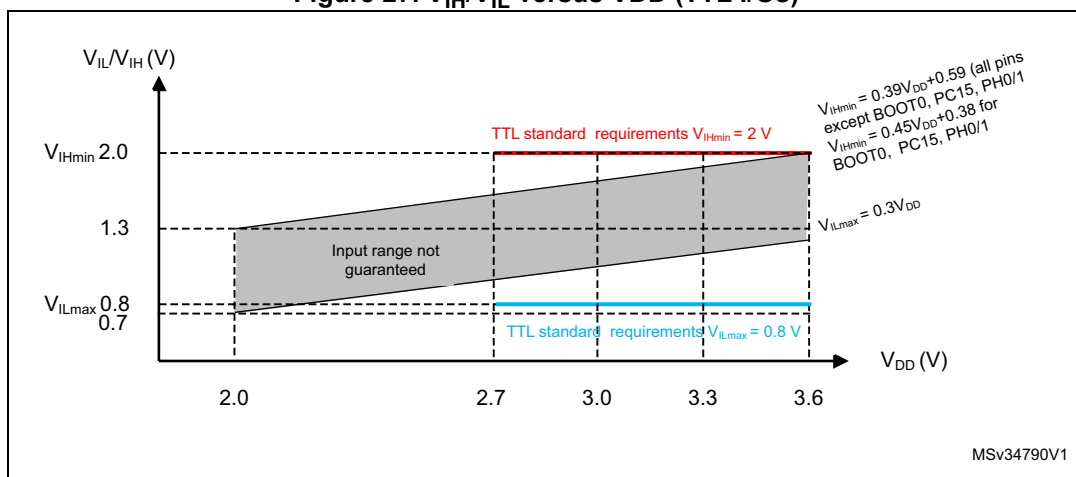
6.3.8 PLL characteristics

The parameters given in [Table 51](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 26](#).

Table 51. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max ⁽¹⁾	
$f_{\text{PLL_IN}}$	PLL input clock ⁽²⁾	2	-	24	MHz
	PLL input clock duty cycle	45	-	55	%
$f_{\text{PLL_OUT}}$	PLL output clock	2	-	32	MHz
t_{LOCK}	PLL input = 16 MHz PLL VCO = 96 MHz	-	115	160	μs
Jitter	Cycle-to-cycle jitter	-		± 600	ps
$I_{\text{DDA(PLL)}}$	Current consumption on V_{DDA}	-	220	450	μA
$I_{\text{DD(PLL)}}$	Current consumption on V_{DD}	-	120	150	

1. Guaranteed by characterization results.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by $f_{\text{PLL_OUT}}$.

Figure 26. V_{IH}/V_{IL} versus V_{DD} (CMOS I/Os)Figure 27. V_{IH}/V_{IL} versus V_{DD} (TTL I/Os)

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 15 mA with the non-standard V_{OL}/V_{OH} specifications given in [Table 61](#).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating $I_{VDD(\Sigma)}$ (see [Table 24](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating $I_{VSS(\Sigma)}$ (see [Table 24](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 61](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 26](#). All I/Os are CMOS and TTL compliant.

Table 61. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ , $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	TTL port ⁽²⁾ , $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin	TTL port ⁽²⁾ , $I_{IO} = -6 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	2.4	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +15 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	1.3	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin	$I_{IO} = -15 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD}-1.3$	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +4 \text{ mA}$ $1.65 \text{ V} \leq V_{DD} < 3.6 \text{ V}$	-	0.45	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin	$I_{IO} = -4 \text{ mA}$ $1.65 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD}-0.45$	-	
$V_{OLFM+}^{(1)(4)}$	Output low level voltage for an FTf I/O pin in Fm+ mode	$I_{IO} = 20 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	
		$I_{IO} = 10 \text{ mA}$ $1.65 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 24](#). The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 24](#). The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
4. Guaranteed by characterization results.

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The simplified formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 65. R_{AIN} max for $f_{ADC} = 16 \text{ MHz}^{(1)}$

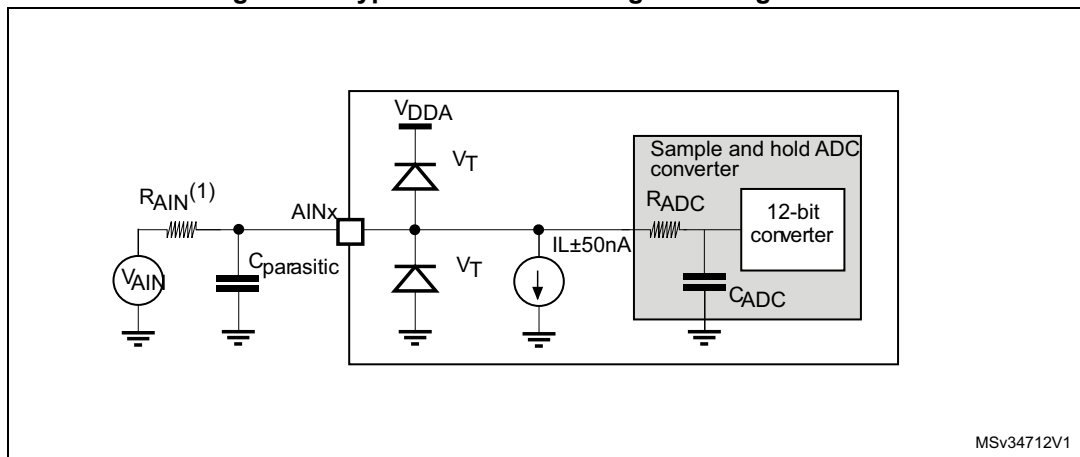
T_S (cycles)	t_S (μs)	R_{AIN} max for fast channels ($k\Omega$)	R_{AIN} max for standard channels ($k\Omega$)						
			$V_{DD} > 2.7 \text{ V}$	$V_{DD} > 2.4 \text{ V}$	$V_{DD} > 2.0 \text{ V}$	$V_{DD} > 1.8 \text{ V}$	$V_{DD} > 1.75 \text{ V}$	$V_{DD} > 1.65 \text{ V}$ and $T_A > -10 \text{ }^\circ\text{C}$	$V_{DD} > 1.65 \text{ V}$ and $T_A > 25 \text{ }^\circ\text{C}$
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1
39.5	2.47	13	12.2	12	10	NA	NA	NA	5
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42

1. Guaranteed by design.

Table 66. ADC accuracy⁽¹⁾⁽²⁾⁽³⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ET	Total unadjusted error	$1.65 \text{ V} < V_{DDA} = V_{REF+} < 3.6 \text{ V}$, range 1/2/3	-	2	4	LSB
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.5	
ENOB	Effective number of bits		10.2	11	-	bits
	Effective number of bits (16-bit mode oversampling with ratio =256) ⁽⁴⁾		11.3	12.1	-	
SINAD	Signal-to-noise distortion		63	69	-	dB
SNR	Signal-to-noise ratio		63	69	-	
	Signal-to-noise ratio (16-bit mode oversampling with ratio =256) ⁽⁴⁾		70	76	-	
THD	Total harmonic distortion		-	-85	-73	

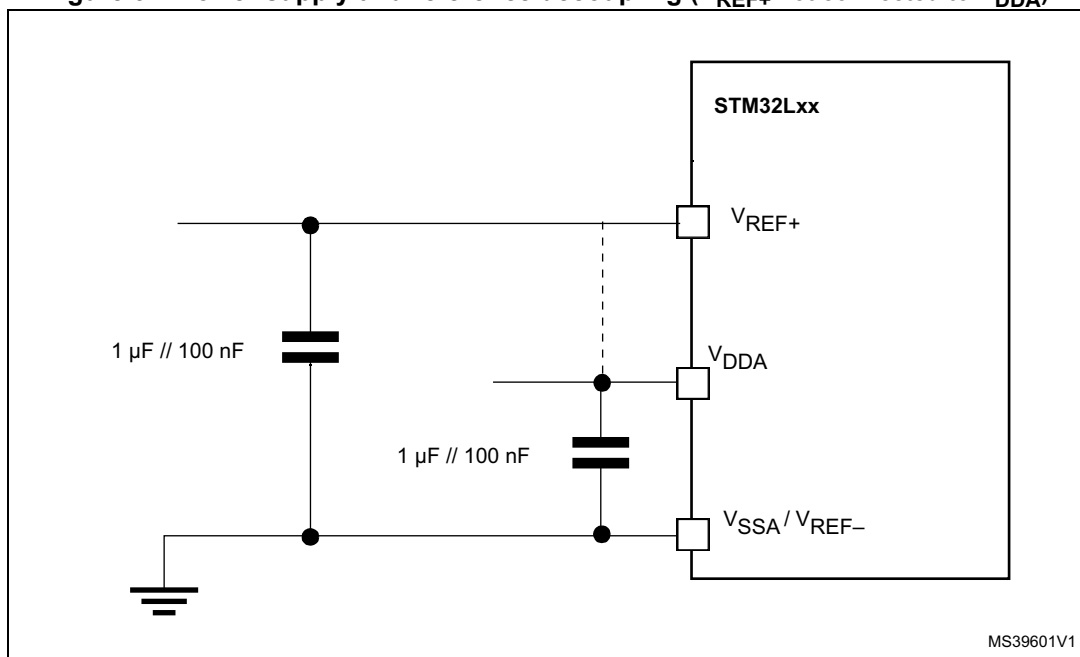
Figure 31. Typical connection diagram using the ADC



1. Refer to [Table 64: ADC characteristics](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 32](#) or [Figure 33](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed as close as possible to the chip.

Figure 32. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

6.3.19 Timer characteristics

TIM timer characteristics

The parameters given in the [Table 72](#) are guaranteed by design.

Refer to [Section 6.3.13: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 72. TIMx characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time		1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32\text{ MHz}$	31.25	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4		0	$f_{TIMxCLK}/2$	MHz
		$f_{TIMxCLK} = 32\text{ MHz}$	0	16	MHz
Res_{TIM}	Timer resolution	-		16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected (timer's prescaler disabled)	-	1	65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32\text{ MHz}$	0.0312	2048	μs
t_{MAX_COUNT}	Maximum possible count	-	-	65536×65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 32\text{ MHz}$	-	134.2	s

1. TIMx is used as a general term to refer to the TIM2, TIM6, TIM21, and TIM22 timers.

6.3.20 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm) : with a bit rate up to 100 kbit/s
- Fast-mode (Fm) : with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+) : with a bit rate up to 1 Mbit/s.

The I²C timing requirements are guaranteed by design when the I²C peripheral is properly configured (refer to the reference manual for details). The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to [Section 6.3.13: I/O port characteristics](#) for the I2C I/Os characteristics).

All I²C SDA and SCL I/Os embed an analog filter (see [Table 73](#) for the analog filter characteristics).

Table 76. SPI characteristics in voltage Range 2 ⁽¹⁾

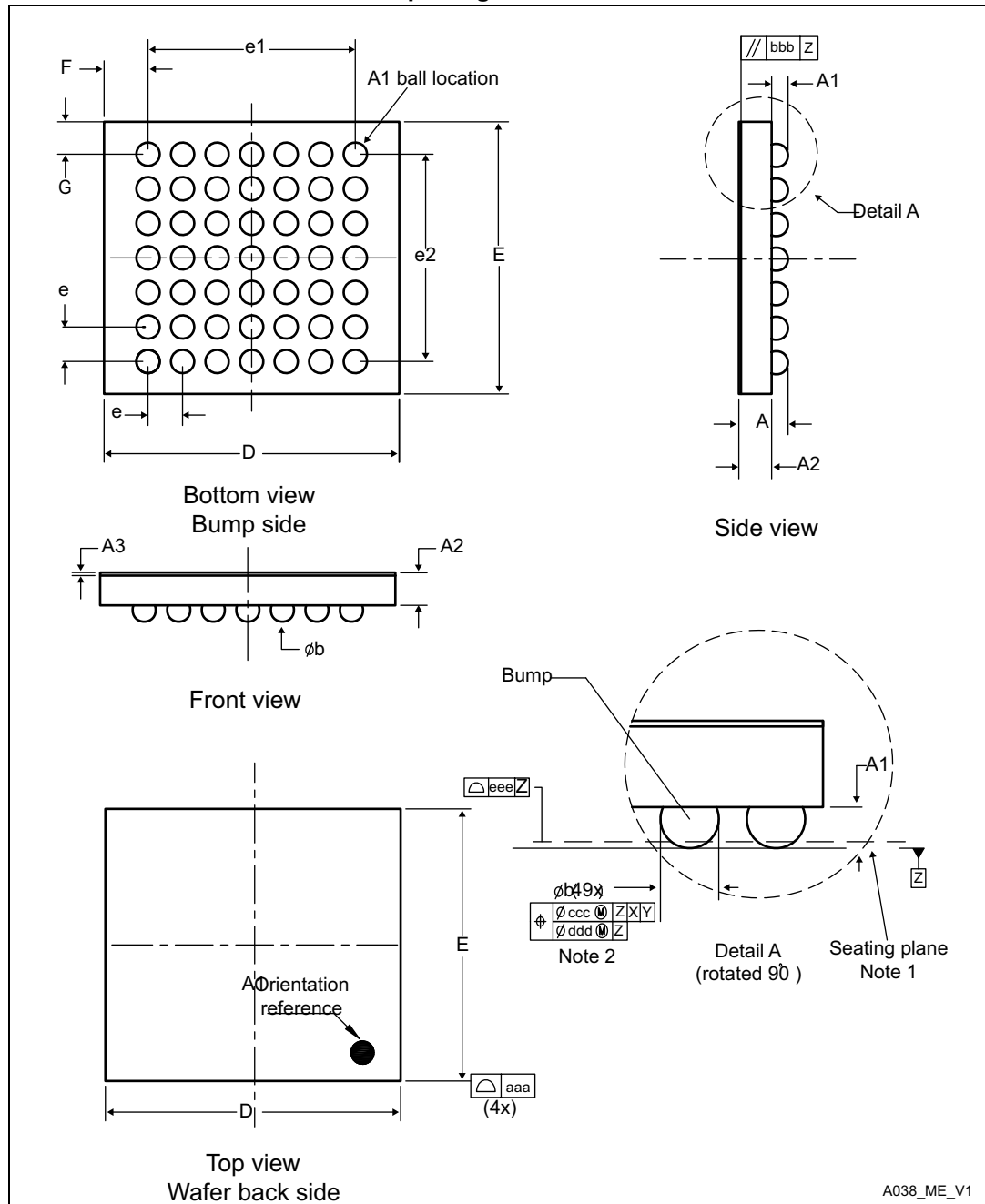
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	-	8	MHz
		Slave mode Transmitter $1.65 < V_{DD} < 3.6V$			8	
		Slave mode Transmitter $2.7 < V_{DD} < 3.6V$			8 ⁽²⁾	
$Duty_{(SCK)}$	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	$4 \cdot T_{pclk}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	$2 \cdot T_{pclk}$	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	$T_{pclk} - 2$	T_{pclk}	$T_{pclk} + 2$	
$t_{su(MI)}$	Data input setup time	Master mode	0	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	11	-	-	
$t_{h(SI)}$		Slave mode	4.5	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	18	-	52	
$t_{dis(SO)}$	Data output disable time	Slave mode	12	-	42	
$t_{v(SO)}$	Data output valid time	Slave mode	-	20	56.5	
$t_{v(MO)}$		Master mode	-	5	9	
$t_{h(SO)}$	Data output hold time	Slave mode	13	-	-	
$t_{h(MO)}$		Master mode	3	-	-	

1. Guaranteed by characterization results.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while $Duty_{(SCK)} = 50\%$.

7.6 WLCSP49 package information

Figure 54. WLCSP49 - 49-pin, 3.294 x 3.258 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.